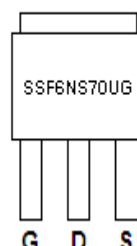
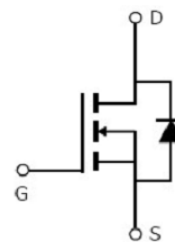


Main Product Characteristics:

V_{DSS}	700V
$R_{DS(on)}$	0.95Ω (typ.)
I_D	6A ①



TO-251 (IPAK)


 Marking and pin
Assignment


Schematic diagram

Features and Benefits:

- High dv/dt and avalanche capabilities
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance


Description:

The SSF6NS70UG series MOSFETs is a new technology, which combines an innovative super junction technology and advance process. This new technology achieves low Rdson, energy saving, high reliability and uniformity, superior power density and space saving.

Absolute max Rating:

Symbol	Parameter	Max.	Units
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V	6 ①	A
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V	3.7 ①	
I_{DM}	Pulsed Drain Current ②	18	
P_D @TC = 25°C	Power Dissipation ③	33	W
	Linear Derating Factor	0.264	W/°C
V_{DS}	Drain-Source Voltage	700	V
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy @ L=100mH	72	mJ
I_{AS}	Avalanche Current @ L=100mH	1.2	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

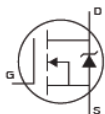
Thermal Resistance

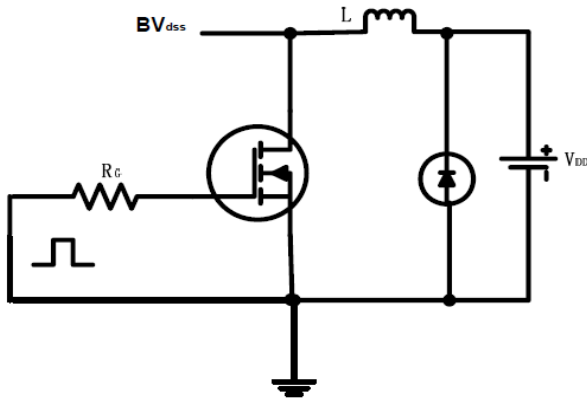
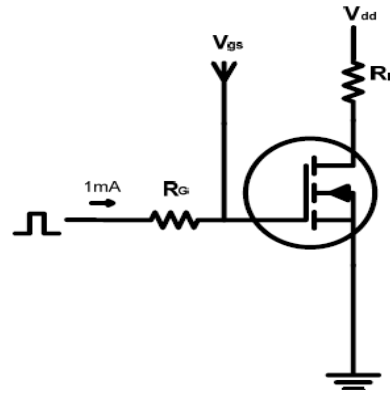
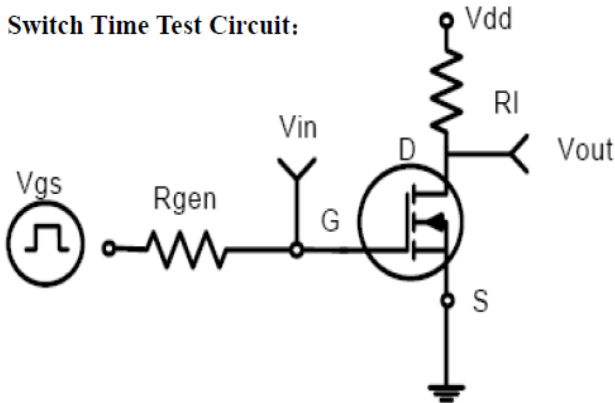
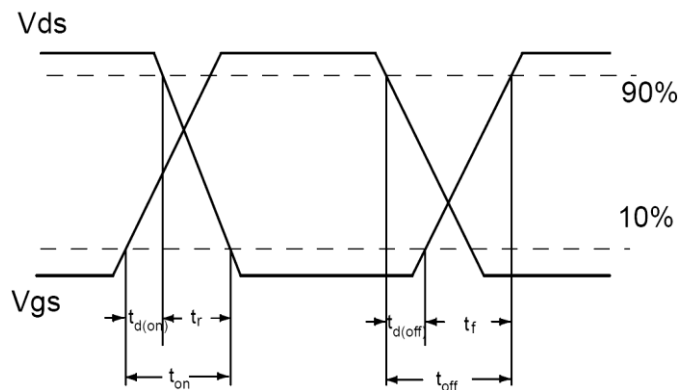
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	3.8	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10\text{s}$) ④	—	62	$^{\circ}\text{C}/\text{W}$

Electrical Characterizes @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

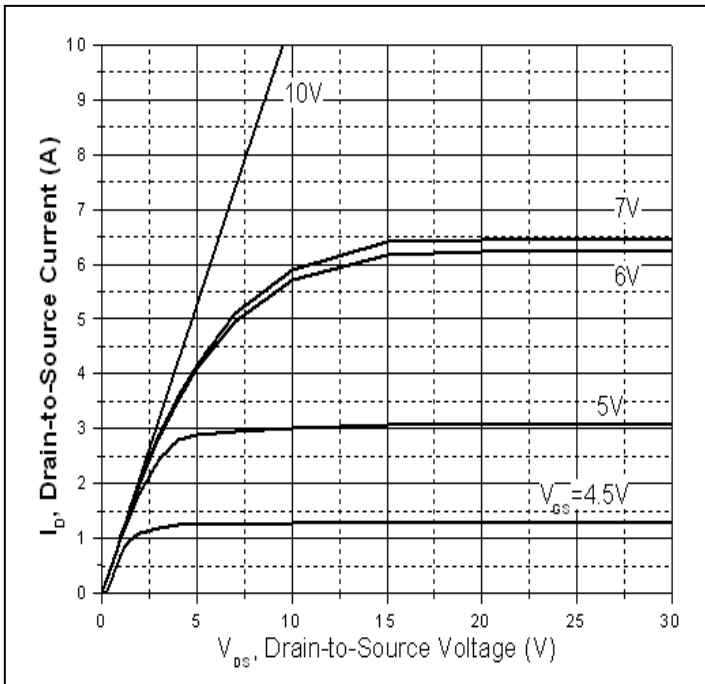
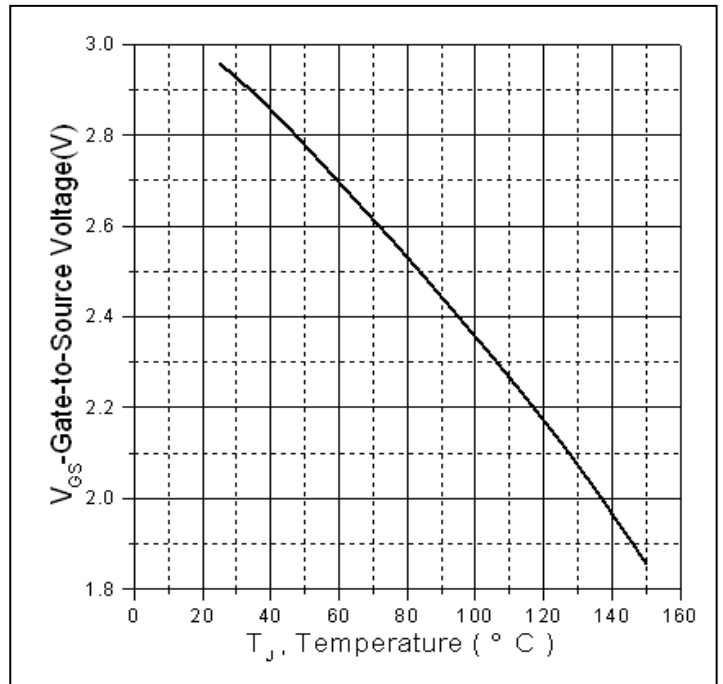
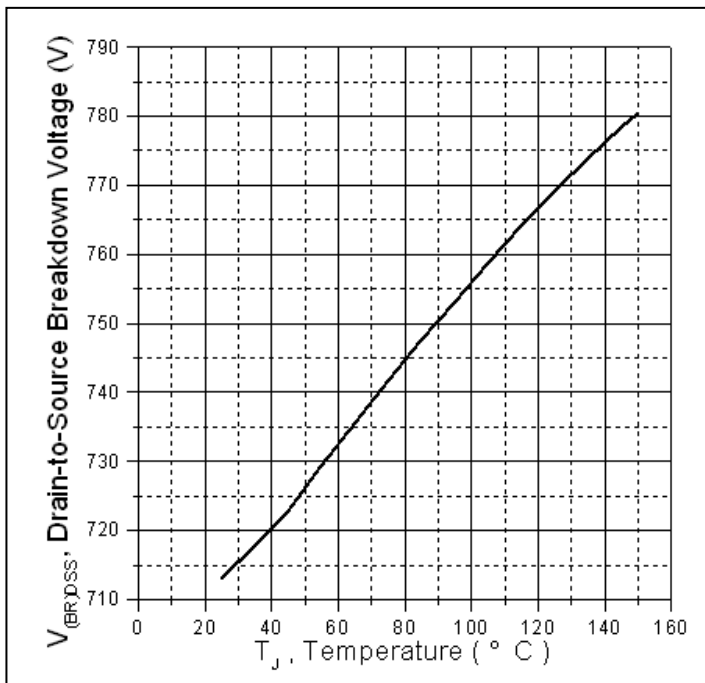
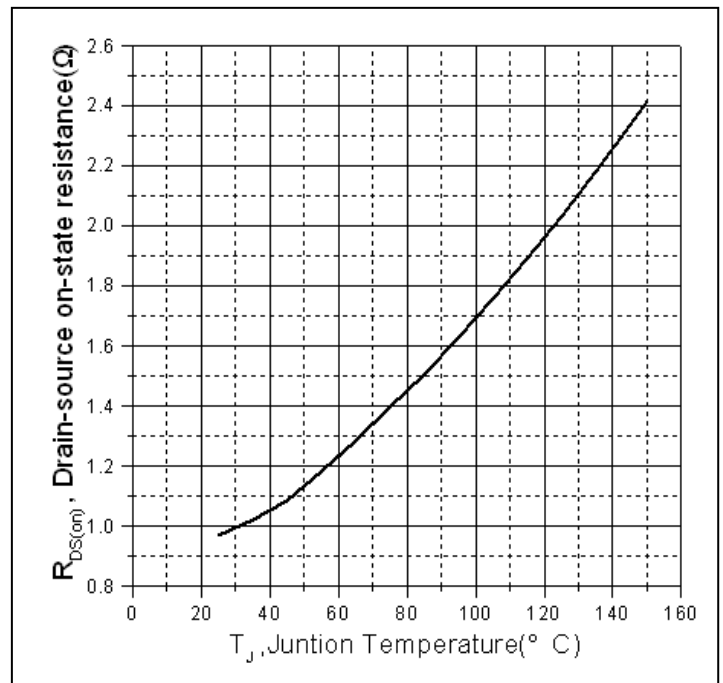
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	700	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	0.95	1.15	Ω	$V_{GS}=10\text{V}, I_D = 1\text{A}$ $T_J = 125^{\circ}\text{C}$
		—	2.0	—		
		—	1.15	1.3	Ω	$V_{GS}=10\text{V}, I_D = 2.8\text{A}$ $T_J = 125^{\circ}\text{C}$
		—	2.1	—		
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ $T_J = 125^{\circ}\text{C}$
		—	2.1	—		
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 700\text{V}, V_{GS} = 0\text{V}$ $T_J = 125^{\circ}\text{C}$
		—	—	50		
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 30\text{V}$ $V_{GS} = -30\text{V}$
		—	—	-100		
Q_g	Total gate charge	—	10.5	—	nC	$I_D = 5\text{A},$ $V_{DS}=200\text{V},$ $V_{GS} = 10\text{V}$
Q_{gs}	Gate-to-Source charge	—	2.8	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	4.5	—		
$t_{d(on)}$	Turn-on delay time	—	8.7	—	ns	$V_{GS}=10\text{V}, V_{DS} = 400\text{V},$ $R_{GEN}=10.2\Omega, I_D = 1.5\text{A}$
t_r	Rise time	—	5.8	—		
$t_{d(off)}$	Turn-Off delay time	—	24	—		
t_f	Fall time	—	14	—		
C_{iss}	Input capacitance	—	338	—	pF	$V_{GS} = 0\text{V}$ $V_{DS} = 100\text{V}$ $f = 1\text{MHz}$
C_{oss}	Output capacitance	—	17	—		
C_{rss}	Reverse transfer capacitance	—	2.7	—		

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	6 ①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	18	A	
V_{SD}	Diode Forward Voltage	—	0.79	1.2	V	$I_S=2.8\text{A}, V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	—	102	—	nS	$T_J = 25^{\circ}\text{C}, I_F = 1.5\text{A},$
Q_{rr}	Reverse Recovery Charge	—	421	—	nC	$di/dt = 100\text{A}/\mu\text{s}$

Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$

Typical electrical and thermal characteristics

Figure 1: Typical Output Characteristics

Figure 2. Gate to source cut-off voltage

Figure 3. Drain-to-Source Breakdown Voltage Vs. Case Temperature

Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical electrical and thermal characteristics

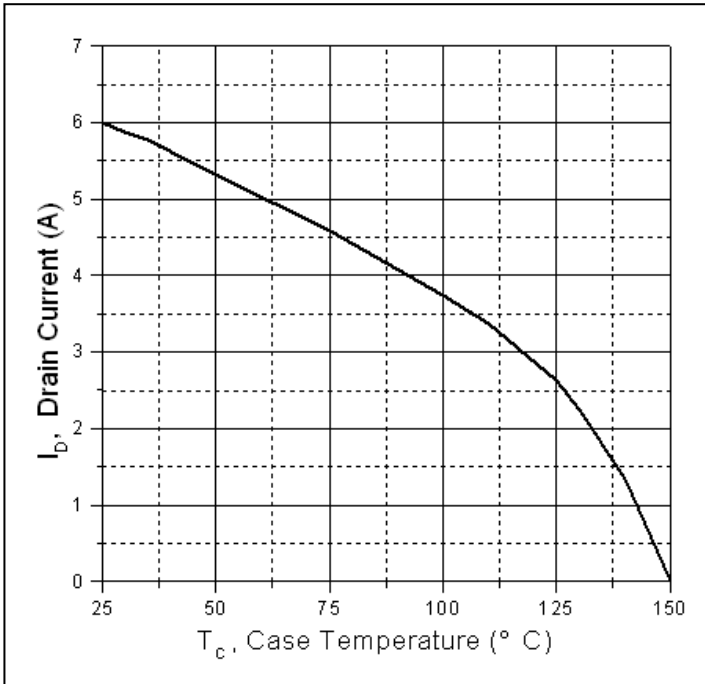


Figure 5. Maximum Drain Current Vs. Case Temperature

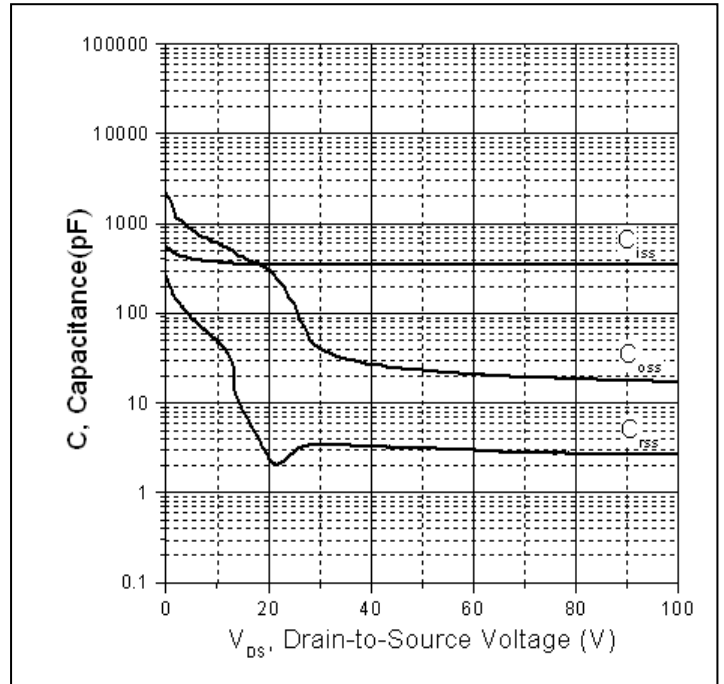


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

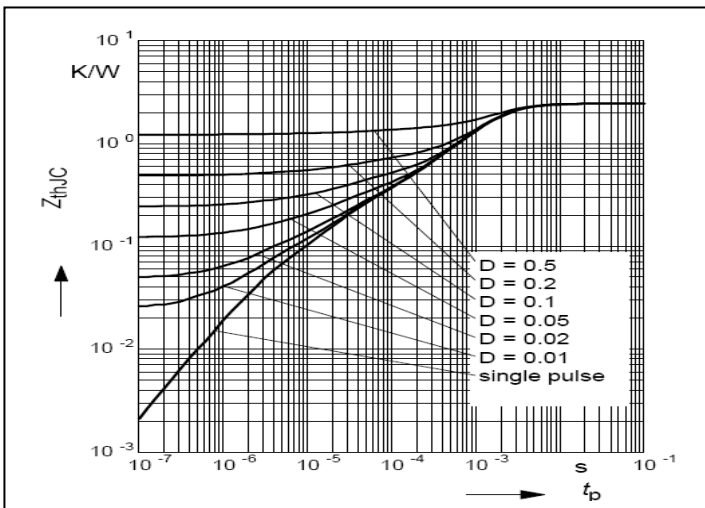
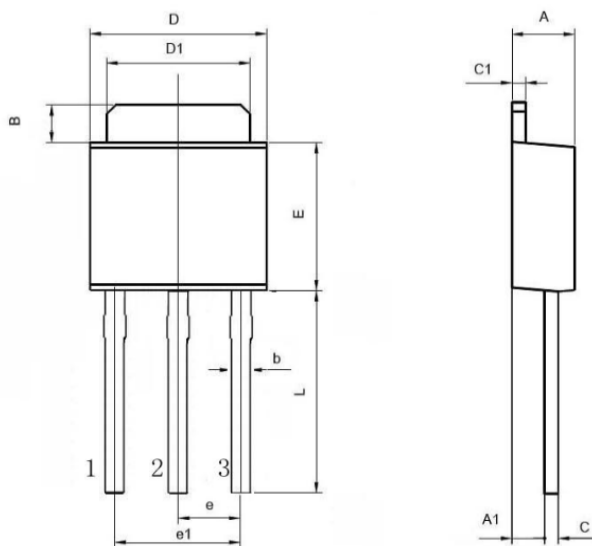


Figure7. Maximum Effective Transient Thermal Impedance Junction-to-Case

Mechanical Data:
TO-251 PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	-	2.400	0.087	-	0.094
A1	0.950	-	1.150	0.037	-	0.045
B	0.950	-	1.250	0.037	-	0.049
b	0.500	-	0.700	0.020	-	0.028
c	0.450	-	0.550	0.018	-	0.022
c1	0.450	-	0.550	0.018	-	0.022
D	6.450	-	6.750	0.254	-	0.266
D1	5.200	-	5.400	0.205	-	0.213
E	5.950	-	6.250	0.234	-	0.246
e	2.240	-	2.340	0.088	-	0.092
e1	4.430	-	4.730	0.174	-	0.186
L	9.000	-	9.400	0.354	-	0.370

Ordering and Marking Information
Device Marking: SSF6NS70UG

Package (Available)
TO-251(IPAK)
Operating Temperature Range
C : -55 to 150 °C

Devices per Unit

Package Type	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-251	75	60	4500	5	225000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T _j =125°C to 150°C @ 80% of Max V _{DSS} /V _{CES} /V _R	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T _j =150°C @ 100% of Max V _{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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